

IN THE SPECIFICATION:

Please replace paragraph number [0002] with the following rewritten paragraph:

[0002] Field of the Invention: The present invention relates to semiconductor device structures including thin layers of conductive materials that are oxidation resistant and that act as oxidation barriers to protect underlying conductive or semiconductive structures. More specifically, the present invention relates to semiconductor device structures ~~including~~ with thin layers with noble metals that have been doped to prevent the passage of oxidants therethrough, as well as to methods for forming such thin, doped noble metal layers. The invention also pertains to the use of electroless plating techniques to form oxidation barrier layers from noble metal alloys.

Please replace paragraph number [0041] with the following rewritten paragraph:

[0041] As shown in FIG. 2, in another embodiment of semiconductor device structure ~~10~~ 10 incorporating teachings of the present invention, which also includes a capacitor 30 under fabrication, an oxidation barrier layer 12 may be located beneath a conductive structure, such as the depicted bottom electrode 14. As oxidation barrier layer 12 is located beneath the conductive structure, it prevents oxidation of underlying conductive or semiconductive structures 32, such as a polysilicon plug or active device region, but does not prevent oxidation of an overlying conductive structure, such as bottom electrode 14. Accordingly, bottom electrode 14 is preferably formed from an oxidation resistant material, such as platinum, ruthenium, ruthenium oxide, rhodium, rhodium oxide, iridium, iridium oxide, palladium, and molybdenum oxide.